# CORRECTION Open Access

# Correction to: Light-Activated Multilevel Resistive Switching Storage in Pt/Cs<sub>2</sub>AgBiBr<sub>6</sub>/ITO/Glass Devices



Tingting Zhong, Yongfu Qin<sup>†</sup>, Fengzhen Lv<sup>\*</sup>, Haijun Qin and Xuedong Tian

# Correction to: Nanoscale Research Letters (2021) 16:178 https://doi.org/10.1186/s11671-021-03636-6

Following the publication of the original article [1], the authors flagged that the equal contribution symbol (†) had been (incorrectly) assigned to the third author in the author list. It has now been (correctly) assigned to the second author in the list, Yongfu Qin, in the original article.

Published online: 12 January 2022

### Reference

 Zhong T, Qin Y, Lv F et al (2021) Light-activated multilevel resistive switching storage in Pt/Cs<sub>2</sub>AgBiBr<sub>6</sub>/ITO/glass devices. Nanoscale Res Lett 16:178. https://doi.org/10.1186/s11671-021-03636-6

## **Publisher's Note**

Springer Nature remains neutral with regard to jurisdictional claims in published maps and institutional affiliations.

The original article can be found online at https://doi.org/10.1186/s11671-021-03636-6

\*Correspondence: Ivfzh17@mailbox.gxnu.edu.cn

†Y. F. Qin: Equal contributor.

School of Physical Science and Technology and Guangxi Key Laboratory of Nuclear Physics and Technology, Guangxi Normal University, Yucai Road, Guilin 541000, China

